Snell's law for surface electrons: R effraction of an electron gas im aged in real space

Jascha Repp $_{1}^{1,2}$ Gerhard Meyer $_{1}^{1,2}$ and Karl-Heinz Rieder²

¹ IBM Research, Zurich Research Laboratory, CH-8803 Ruschlikon, Switzerland

² Institut fur Experim entalphysik, Freie Universitat Berlin, Arnim allee 14, D-14195 Berlin, Germ any

(Dated: April 14, 2024)

0 n N a C 1(100)/C u (111) an interface state band is observed that descends from the surface-state band of the clean copper surface. This band exhibits a Moire-patterm-induced one-dimensional band gap, which is accompanied by strong standing-wave patterns, as revealed in low-temperature scanning tunneling microscopy im ages. A t N a C lisland step edges, one can directly see the refraction of these standing waves, which obey Snell's refraction law.

PACS num bers: 68.37 Ef, 73.20 At, 73.61 Ng

Ever since the mapping of standing waves of a twodimensional electron gas (2DEG) on the close-packed Cu (111) surface by means of low-tem perature scanning tunneling m icroscopy (LT-STM) [1,2], the 2DEG turned out to be an ideal playground for a variety of LT-STM experim ents [3, 4, 5, 6, 7, 8, 9, 10, 11, 12]. In the STM im ages the surface electrons reveal their wave-like behavior, often discussed in analogy to light. This analogy has been addressed directly in experim ents such as the connem ent of a 2D E G between two parallel step edges, considered as a counterpart of the optical Fabry-Perot resonator $[\beta]$, the striking experiment of an electronic M ach-Zehnder interferom eter [4], and the spectacular quantum m irage experim ent [5]. How ever, despite this strong analogy, the counterpart of optical refraction has not yet been observed for surface electrons.

Such an experim ent has to com ply with several requirem ents. First of all, two di erent m edia are necessary. For surface electronic states, two regions having di erent dispersionsm ay act as the media and be realized by a partial coverage of the surface with an adlayer that modi es the dispersion, as was observed for various thin m etal lm s on Cu(111) [6, 7, 8, 9] as well as for Xe/Cu(111) [10]. Second in terms of optics the interface between the two media has to be transparent. It was reported that step edges of m etals exhibit a transm ission close to zero for surface electrons, i.e., that the wave patterns on the two sides of a step edge are not related to each other [3]. However, in the case of an insulator adsorbed on a metal surface, this m ay be di erent: A n insulator does not contribute to the electronic states, therefore the electrons are still con ned to the surface of the m etal underneath, and thus may better overlap with the electrons of the clean surface. Third, in addition to being inherently transparent, the interface between the two media also has to be very smooth. This means that a perfect step edge is needed to observe refraction of surface electrons.

A s N aC 1/C u (111) m cets the above requirem ents, we are able to report here the st observation of the refraction of surface electronic waves at island step edges by m eans of LT-STM . M oreover, we show that natural M oire patterns, inherent in incom m ensurate grow th, gen-

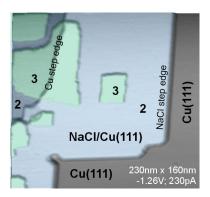


FIG.1:STM image of NaClon Cu(111). The numbers indicate the thickness of the NaCl islands in layers.

erate a band gap within a two-dimensional (2D) interface state band. Thereby the textbook band-structure model of nearly free electrons (NFE) is exploited and visualized in real space.

O ur experim ents were perform ed w ith a LT-STM [13] operated at 9 K. The sam ple was cleaned by several sputtering and annealing cycles. NaClwas evaporated therm ally, while the sam ple tem perature was kept at 320 K. B ias voltages refer to the sam ple voltage w ith respect to the tip, and we used electrochem ically etched tungsten w ire as STM tips.

N aCl forms (100)-term inated islands that are up to several microns in diameter [14] (see Fig. 1). The N aCl islands start with a double-layer thickness and perfect nonpolar step edges, in which the anions and the cations alternate. On top of the initial double layer, islands of additional layers are form ed. Substrate defect steps are smoothly overgrown in the so-called carpetlike growth [15]. Because of the di erent symmetries of N aCl(100) and Cu(111), the growth is incommensurate. In the case of only a few layers of N aCl, the nonvanishing tail of charge density from the metal that extends through the insulator is su cient to take STM im – ages without crashing the tip. In atom ically resolved STM im ages, only the Cl ions are imaged as protrusions [16, 17, 18].

Upon adsorption of NaCl, the Cu (111) surface state band survives and forms an interface state band that is con ned to the insulator/m etal interface and has a larger Ferm i wavelength of $_{\rm F}$ = 3:8 nm (clean Cu: $_{\rm F}$ = 3:0 nm). To measure the dispersion of this modi ed 2D interface state band, di erential conductance (dI/dV) im ages were taken at various bias voltages, as shown in Figs. 2(a)-(d). By extracting the wavelength of the wave patterns seen in these in ages [19], the dispersion relation can be established (see Fig. 2(e)), as was done for the clean Cu surface [1, 2, 20]. The band minimum E₀ was obtained by recording the dI/dV signal at a xed position as a function of energy [20, 21] (crosses in Fig. 2 (e)) and is shifted upward in energy by (230 30) m eV in the case of the adsorption of an insulating NaCl overlayer. The resulting parabolic dispersion $E = E_0 + (hk)^2 = 2m$ is slightly wider, i.e., the e ective mass m has increased from $(0:40 \quad 0:02)$ m_e to $(0:46 \quad 0:04)$ m_e, where m_e denotes the free electron m ass.

The energy shift can be qualitatively understood within the one-dimensional (1D) phase-accumulation m odel [22, 23]. In this analysis, the wave function of surface electrons is found by m atching the wave-function phase of the analytical solution inside the copper crystal [24] to the one of the num erical solution for the outside region, obtained by integrating the Schrodinger equation [22]. For the latter an electrostatic potential had to be assumed: For the clean Cu surface, this is given by the image potential [25]. For N aC l/Cu (111) we considered the m odi ed image potential [23, 25] as well as the low ering of the work function upon N aC ladsorption [14].

This model yields an upward shift of the dispersion of E ' 300 m eV, in qualitative agreem ent with our experim ent. E ven m ore relevant, it reveals that the wave functions of the surface electrons are barely modi ed upon adsorption of NaCl (see Fig. 2 (f)) and thus render a high transm ission through NaClstep edges prom ising. Moreover, it justi as an even simpler understanding of the upward shift in the dispersion within rst-order perturbation theory, E = h j V j i. Owing to the exponentially decaying wave function outside the Cu substrate, the perturbation potential V, i.e., the potential di erence with and without NaCl, is only relevant for the energy shift E in immediate proximity of the copper surface. The upward shift thus results from the positive perturbation potential at the interface given by the weaker in age potential [25] due to the polarization of the adsorbed dielectric. The work-function change [14] as well as the in age potential at the insulator-to-vacuum interface are negligible for E. Consequently, the dispersion for three layers of N aC l does not dier from that for two layers, which was veried in the experiment.

The above results show that for interface states of an insulator/m etal system, as described here, the main contribution of the electronic wavefunctions resides within the substrate (see Fig. 2 (f)). Therefore, the electric

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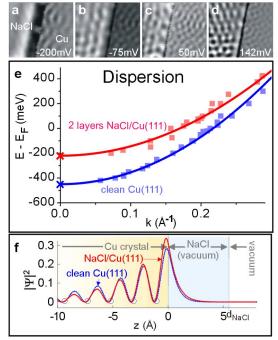


FIG.2: (a) to (d) dI/dV in ages of the same region near a N aCl step edge, taken at various voltages. In all cases the wavelength of the N aC l/C u (111) interface state is larger than that of the C u (111) surface state. (e) D ispersion of the 2D EG for the clean C u (111) surface and the N aC l(100)/C u (111) interface state band (square data points and t curves). (f) U sing the phase-accum ulation m odel, the probability distributions j j² perpendicular to the surface are determ ined, yielding only sm all changes upon the adsorption of N aC l. The origin (z = 0) was chosen to be the C u (111) substrate surface. C incles denote the position of C u atom s.

m ass of the shifted interface state will mainly be determ ined by the metal. For copper an upward shift of the surface state is expected to be correlated with a slight increase of the e ective mass as discussed in Ref. [22], in good agreement with the present experiment. The energetic shift of the band for other insulator/metal systems will depend critically on the structure of the interface. However, the adsorption of an insulator that does not strongly a ect the metal surface but weaken its im age potential will in general result in an upward shift of the surface state band. These ndings explain that in a previous experiment on X e/C u (111) [10] a sim ilar upward shift and e ective mass increase were observed.

A nother condition for the observation of the electron refraction at island edges is the presence of standing waves. Continuous waves lead to a uniform probability distribution and thus prevent the observation of refraction in the STM images, even if the refraction took place. In the case of N ac l/C u (111), strong electronic plane waves are already inherent in the system : The incommensurate growth gives rise to various M oire patterns [26], which can be seen in atom ically resolved STM

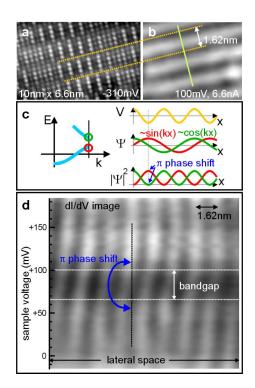


FIG. 3: (a) An atom ically resolved STM in age shows one of the various possible M oire patterns that result from incommensurate growth [26]. (b) This pattern gives rise to a strong plane-wave pattern. (c) Illustration of a band gap in the NFE m odel. Just below and just above the band gap (m arked by circles), the electronic wave functions are expected to be standing waves, and the probability distributions $j j^2$ willhave a phase shift of with respect to each other. (d) This dI/dV in age (acquired in constant-height m ode) m aps the probability distribution $j j^2$ in real space and energy. It shows the behavior expected from the NFE m odel.

im ages (Fig. 3(a)). The Moire patterns will be associated with displacem ents of the charged ions and are thus accom panied by a modulation of the electrostatic potential seen by the surface electrons. One general conclusion of the NFE model [27] is that any periodic potential modulation will give rise to a band gap. Just below and just above the band gap, the electronic wave functions are expected to be standing waves, and the probability distributions j j² will have a phase shift of with respect to each other, as illustrated in Fig. 3(c). For the case discussed here, this physics textbook statem ent can be imaged in real space. As a rst indication, STM im ages such as that in Fig. 3(b) show strong standing plane waves that correspond to this particular Moire pattem in terms of wavelength and direction (dotted lines in Fig. 3(a) and (b)).

For a more precise analysis, we recorded an dI/dV image in constant-height mode, but whereas we scanned within one scan line perpendicular to the plane waves (as indicated by the solid line in Fig. 3 (b)), we did not move the tip in the other direction. Instead, we changed

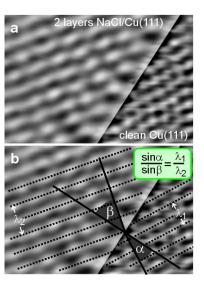


FIG.4: (a) STM dI/dV in age (constant-current mode) of a N aCl island step edge reveals strong standing-wave patterns, not only on the N aCl island but also on the clean Cu (111) surface (V = 55 mV). (b) Adding some lines as guide to the eye shows that the standing-wave pattern obeys Snell's refraction law. Note that the contrast for the area of clean Cu (111) is increased, com pared with the rest of the im age.

the bias voltage after each scan line. The resulting STM image in Fig. 3 (d) thus rejects a map of the probability distribution j j² in space and energy. As expected, the image shows a region of reduced intensity, which represents the band-gap region. Just above and just below this region, there are strong standing-wave patterns shifted by to each other.

The standing-wave pattern caused by a periodic scattering potential contains only the wavelength components of this potential modulation. Thus in Fig. 3(d), the standing-wave pattern is given by the Moire pattern's periodicity and does not change with energy. The position in energy of the band gap can vary between 20 and 400 m eV above the Ferm i level from one rotational domain to the next. In all cases, this energy position can be linked to the M oire patterns in such a way that the wave vector at the band gap corresponds to half of the wave vector of the potential modulation, in agreement with the NFE model. In the particular case shown in Fig. 3 the Moire pattern has a periodicity of ' 1:62 nm corresponding to $k = 2 = 162 \text{ A}^{-1}$, $k_{qap} = 0.194 \text{ A}^{-1}$, and thus E_{gap} ' 81 m eV . As this condition is met only in one direction, we have a 1D band gap in a 2D electron gas, i.e., a pseudo gap. For som e rotational dom ains, the condition was not met in the experimentally accessible energy range, and no band gap was observed, as in the case of the dispersion shown in Fig. 2 (e).

The standing-wave pattern persists far above the band gap because of the one-dimensionality of the band gap. This is also one of the reasons for the remaining low intensity within the band gap. In addition, the nite lifetime of the interface states [11] gives rise to an energetic broadening of the states, which further $\mbox{sm ears out}$ " the bandgap and m ay also lead to interference e ects.

To observe the refraction, we took advantage of the strong standing plane waves just below the band gap by applying a corresponding bias voltage of V = 55 meV. Figure 4 shows the refraction of the surface electrons in a di erential conductance (dI/dV) in age of an island edge of NaCl/Cu (111). The region on the NaCl island (to the left) show s a strong standing plane-wave pattern that is due to the form ation of a band gap. Re ection induces an additional modulation of the pattern parallel to the step edge. M ore importantly, the image clearly reveals standing plane waves on the clean copper surface (to the right). These patterns at the island step edge obey Snell's refraction law, $\sin() = \sin() = 1 = 2$. Note that and 2 are given by the geom etry of this particular M oire pattern, 1 is the electron wavelength on the clean Cu surface corresponding to $E = E_F + 55 \text{ meV}$, and is given by Snell's law. This law follows directly from the conservation of the component of the momentum (and wavelength) parallel to the step. In other words, the patterns on both sides have a xed phase correlation at the step edge, which is directly evident in the images and follows from the postulation of continuous wave functions in quantum mechanics.

In everyday life, optical refraction manifests itself in the bending of light rays, and we cannot observe the wave fronts directly. In F ig. 4 we do not observe the bending of rays, but directly in age the wave fronts, visualizing the refraction m odel. A nother di erence to optics is evident: In optics the refraction is usually determ ined by one term only, namely, the refractive index of the medium. In the case of electron refraction, the band m inimum as well as the electrons may change and thus contribute to the refraction in di erent ways.

The observed band-gap form ation due to M oire patterns is sim ilar to the superlattice concept [28, 29] based on the idea of creating arti cial, tunable 1D band gaps by growing a vertical lattice of alternating sem iconductors. W hereas in sem iconductor superlattices the band gaps can be tuned by the layer thicknesses during grow th, M oire-pattern-induced band gaps can be tuned by the choice of lattice constant m ism atch. This phenom enon show s a new way to tailor the properties of a 2D EG for future applications. These possibilities can be further extended by controlled sequential grow th of di erent dielectric m aterials. In contrast to surface states, interface states are inherently protected by the dielectric adlayer and can even be studied under am bient conditions.

In sum m ary, we observed the form ation of a 1D band gap in the 2D electron gas of the N aC 1/C u (111) interface state band. The band gap is due to the M oire patterns of the incom m ensurate grow th and was observed in an STM im age displaying the electron-probability distribution in space and energy. At NaCl island edges, the refraction of standing waves could be observed, obeying Snell's refraction law.

W e thank Frank Forstm ann and Rolf A llenspach for fruitful discussions, and acknow ledge partial funding by the EU-TMR projects AMM IST " and NANOSPEC-TRA" and the D eutsche Forschungsgem einschaft P roject No.RI 472/3-2.

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